Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3212	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/12 19:39
L2	2089	1 and (trench$2 or groov$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:43
L3	2021	2 and (((ion near2 implant$5) or dop$3) near5 ((trench$2 or groov$2) near2 fill$3) or dielectric or insulat$3 or fill$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:52
L4	1631	3 and (planar$7 or (cmp or (chemical near2 polish$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:49
L5	367	4 and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:50
L6	2021	2 and (((ion near2 implant$5) or dop$3) near ((trench$2 or groov$2) near2 fill$3) or dielectric or insulat$3 or fill$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:52
S1	2	apparatus$2 same (barrier near2 (layer or film)) same trench$2 same (dielectric near2 (layer or film)) same ((ion near2 implant$5) or dop$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 17:03
S2	1107	apparatus$2 and (barrier near2 (layer or film)) and trench$2 and (dielectric near2 (layer or film)) and ((ion near2 implant$5) or dop$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:43
S3	5	apparatus$2 same((barrier near2 (layer or film)) and trench$2 and (dielectric near2 (layer or film)) and ((ion near2 implant$5) or dop$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:05

S4	9	("5897368" | "6110817" | "6218303" | "6239021" | "6258695" | "6300236" | "6340633" | "6342447" | "6352938" | "2001/0010401").PN.	USPAT	OR	OFF	2004/09/10 16:07
S5	1373	apparatus$2 near5 trench$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:12
S6	2500	apparatus$2 with trench$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:12
S7	62	(apparatus$2 with trench$2) and (barrier near2 (layer or film)) and (dielectric near2 (layer or film))and ((ion near2 implant$5) or dop$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 20:01
S8	108	isaac-stanetta.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:29
S9	4	"6713385"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 17:04
S10	3043	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/12 19:39
S11	4	(((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.) and (apparatus$2 with trench$2) and (barrier near2 (layer or film)) and (dielectric near2 (layer or film))and ((ion near2 implant$5) or dop$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 20:01
S12	194	apparatus same ((trench$3 or groov$3) near3 (silicon near2 (wafer$1 or substrate$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 12:58

S13	30	S12 and (((ion near2 implant$5) or dop$3) same (dielectric or insulat$3 or fill$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:05
S14	4230	apparatus same (((ion near2 implant$5) or dop$3) same (dielectric or insulat$3 or fill$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:17
S15	46	S14 and (((trench$3 or groov$3) near3 (silicon near2 (wafer$1 or substrate$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:09
S16	2764	(((ion near2 implant$5) or dop$3) near3 (dielectric or insulat$3 or fill$3)) same (trench$3 or groov$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:21
S17	383	S16 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:19
S18	360	S17 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:20
S19	1566	(((ion near2 implant$5) or dop$3) near3 (dielectric or insulat$3)) same (trench$3 or groov$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 15:20
S20	232	S19 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:21

S21	221	S20 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:21
S22	1161	((ion near2 implant$5) or dop$3) near3 ((dielectric or insulat$3) near2 (layer$1 or film$1)) same (trench$3 or groov$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 15:22
S23	154	S22 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 15:23